

Silicon NPN Power Transistors

2SC2928

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For high voltage,high speed and high power switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

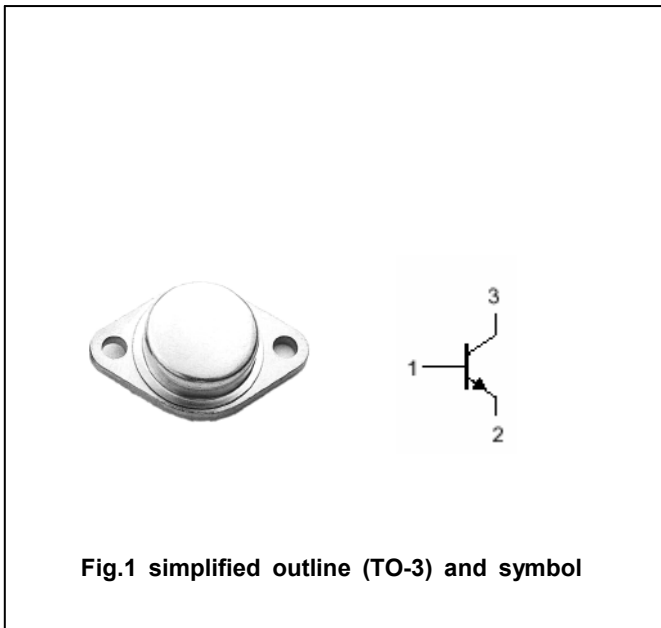


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		7	A
I _B	Base current		2.5	A
P _C	Collector power dissipation	T _C =25℃	80	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-45~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =0.2A ; R _{BE} =∞	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA ; I _C =0	7			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =1.5A ; I _B =0.3A			1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =1.5A ; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1200V ; I _E =0			100	μA
I _{CEO}	Collector cut-off current	V _{CE} =650V ; R _{BE} =∞			100	μA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =3A ; V _{CE} =5V	7			

Switching times

t _{on}	Turn-on time	I _C =3.0A ; V _{CC} =250V I _{B1} =0.6A , I _{B2} =-1.5A			1.0	μs
t _s	Storage time				3.0	μs
t _f	Fall time				1.0	μs

PACKAGE OUTLINE

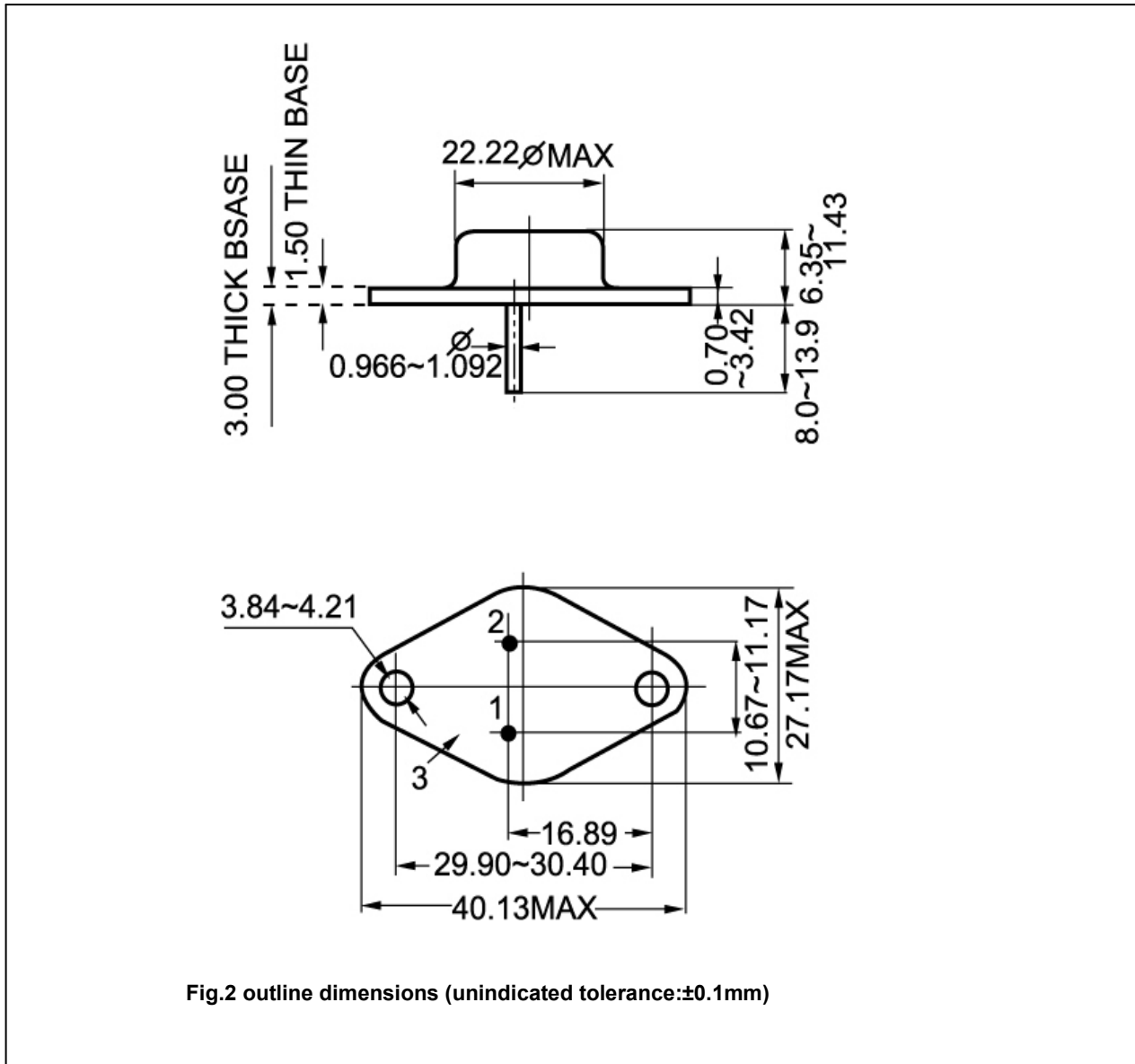


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)